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Kind regards,

Team Nexperia

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

Rev. 04 — 17 February 2005

Product data sheet

1. Product profile

1.1 General description

NPN resistor-equipped transistors.

Table 1: Product overview

Type number	Package	PNP complement	
	Philips	JEITA	
PDTC115TE	SOT416	SC-75	PDTA115TE
PDTC115TK	SOT346	SC-59A	PDTA115TK
PDTC115TM	SOT883	SC-101	PDTA115TM
PDTC115TS ^[1]	SOT54 (TO-92)	SC-43A	PDTA115TS
PDTC115TT	SOT23	-	PDTA115TT
PDTC115TU	SOT323	SC-70	PDTA115TU

Reduces component count

Circuit drivers

Reduces pick and place costs

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistor
- Simplifies circuit design

1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Ι _Ο	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		70	100	130	kΩ

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NPN resistor-equipped transistors; R1 = 100 kΩ, R2 = open

2. Pinning information

Dim	Description		Cumhal
	Description	Simplified outline	Symbol
50154	· · · //		
1	input (base)		
2	OUTPUT (collector)		
3	GND (emitter)		
		001aab347	3
			006aaa218
SOT54A			
1	input (base)		
2	output (collector)		2
3	GND (emitter)		
		001aab348	3
			006aaa218
SOT54 var	iant		
1	input (base)		
2	output (collector)	-tea	2
3	GND (emitter)		
		001aab447	3
			006aaa218
SOT23, SC	DT323, SOT346, SOT416		
1	input (base)		
2	GND (emitter)	3	3
3	output (collector)		
		1 2	2
		<i>006aaa</i> 144	sym012
SOT883			
1	input (base)		
2	GND (emitter)		3
3	output (collector)	2	
		Transparent top view	
			2
			sym012

9397 750 14021 Product data sheet NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

3. Ordering information

Table 4: Orde	Table 4: Ordering information						
Type number	Package	Package					
	Name	Description	Version				
PDTC115TE	SC-75	plastic surface mounted package; 3 leads	SOT416				
PDTC115TK	SC-59A	plastic surface mounted package; 3 leads	SOT346				
PDTC115TM	SC-101	leadless ultra small plastic package; 3 solder lands; body $1.0\times0.6\times0.5~\text{mm}$	SOT883				
PDTC115TS ^[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54				
PDTC115TT	-	plastic surface mounted package; 3 leads	SOT23				
PDTC115TU	SC-70	plastic surface mounted package; 3 leads	SOT323				

[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5: Marking codes	
Type number	Marking code [1]
PDTC115TE	17
PDTC115TK	28
PDTC115TM	G5
PDTC115TS	TC115T
PDTC115TT	*AK
PDTC115TU	*17

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

5. Limiting values

Table 6: L In accordance	.imiting values we with the Absolute Maximun	n Rating System (IEC 60)134).		
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
lo	output current (DC)			-	100	mA
I _{CM}	peak collector current			-	100	mA
P _{tot}	total power dissipation					
	SOT416	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>	-	150	mW
	SOT346	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>	-	250	mW
	SOT883	$T_{amb} \le 25 \ ^{\circ}C$	[2] [3]	-	250	mW
	SOT54	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>	-	500	mW
	SOT23	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>	-	250	mW
	SOT323	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>	-	200	mW
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C

[1] Refer to standard mounting conditions.

[2] Reflow soldering is the only recommended soldering method.

[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 µm copper strip line.

6. Thermal characteristics

Table 7:	Thermal characteristics	5				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> -	-	833	K/W
	SOT346		<u>[1]</u> _	-	500	K/W
	SOT883		[2] [3]	-	500	K/W
	SOT54		<u>[1]</u> -	-	250	K/W
	SOT23		<u>[1]</u> -	-	500	K/W
	SOT323		<u>[1]</u> _	-	625	K/W

[1] Refer to standard mounting conditions.

[2] Reflow soldering is the only recommended soldering method.

[3] Refer to SOT883 standard mounting conditions; FR4 printed-circuit board with 60 µm copper strip line.

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

7. Characteristics

Table 8: Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	1	μA
cut-c	cut-off current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		70	100	130	kΩ
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	-	-	2.5	pF



NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

8. Package outline



Rev. 04 — 17 February 2005

Philips Semiconductors

PDTC115T series

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open



9. Packing information

Table 9:Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PDTC115TE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC115TK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC115TM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTC115TS	SOT54	bulk, straight leads	-	-412	-
PDTC115TS	SOT54A	tape and reel, wide pitch	-	-	-116
PDTC115TS	SOT54A	tape ammopack, wide pitch	-	-	-126
PDTC115TS	SOT54 variant	bulk, delta pinning	-	-112	-
PDTC115TT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTC115TU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

[1] For further information and the availability of packing methods, see Section 14.

NPN resistor-equipped transistors; R1 = 100 kΩ, R2 = open

10. Revision history

Table 10: Revision hi	story				
Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PDTC115T_SER_4	20050217	Product data sheet	-	9397 750 14021	PDTC115TT_3
Modifications	 The types added. 	PDTC115TE, PDTC115	5TK, PDTC115TM, PI	DTC115TS and PDT	C115TU were
	 Table 1 "Pi 	oduct overview" added			
	• Figure 1 a	nd <u>2</u> added			
	Section 9 [•]	Packing information" ac	lded		
PDTC115TT_3	20040727	Product data sheet	-	9397 750 13505	PDTC115TT_2
PDTC115TT_2	20040510	Objective data sheet	-	9397 750 13206	PDTC115TT_1
PDTC115TT_1	20040305	Objective data sheet	-	9397 750 12554	-

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = open

11. Data sheet status

Level	Data sheet status [1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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PDTC115T series

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15. Contents

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 3
4	Marking 3
5	Limiting values 4
6	Thermal characteristics 4
7	Characteristics 5
8	Package outline 6
9	Packing information7
10	Revision history 8
11	Data sheet status
12	Definitions 9
13	Disclaimers 9
14	Contact information9



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